

Q1
current - drain voltage characteristic or the like. In order to suppress the floating-body effect, an isolation oxide film (partial oxide film) is formed in an upper layer portion so as not to come in contact with the buried oxide film and constitutes a partial isolation region together with a part of an SOI layer in a lower layer portion and a body terminal is provided in a body region formed in a region isolated in the partial isolation region. Consequently, a partial isolation technique capable of fixing a substrate potential (body potential) through the SOI layer provided under the partial oxide film is effective. However, there is a problem in that the partial isolation technique does not have the latch up free which is the advantage of the complete isolation technique.

Please amend the specification at page 18, line 22 through page 19, line 1 as shown below:

Q2
Moreover, a body region 10 (a body region outside an element formation region) is isolated by the partial oxide film 31 and the p well region 11 provided thereunder and is formed from the surface of the SOI layer 4 to the back face thereof. The body region 10 is electrically connected to a main part of the body region to be the SOI layer 4 provided under the gate electrode 7 through the p well region 11.

IN THE CLAIMS

Please cancel Claim 2 without prejudice or disclaimer.

Please amend Claims 1 and 3-6 as shown in clean form below:

Q3
1. (Amended) A semiconductor device having an SOI structure including a semiconductor substrate, a buried insulating layer and an SOI layer, comprising:
a MOS transistor provided in an element formation region of said SOI layer; and
a partial isolation region provided in said SOI layer and serving to isolate said